

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC4541

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

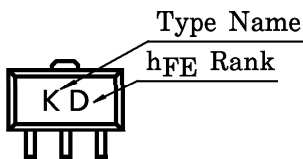
- Low Saturation Voltage :  $V_{CE(sat)} = 0.5V$  (Max.) ( $I_C = 1.5A$ )
- High Speed Switching Time :  $t_{stg} = 0.5\mu s$  (Typ.)
- Small Flat Package
- $P_C = 1\sim 2W$  (Mounted on Ceramic Substrate)
- Complementary to 2SA1736

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

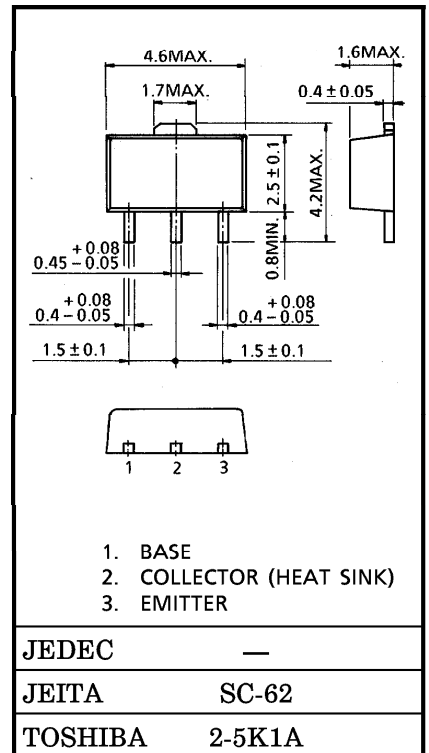
| CHARACTERISTIC              | SYMBOL       | RATING  | UNIT       |
|-----------------------------|--------------|---------|------------|
| Collector-Base Voltage      | $V_{CBO}$    | 80      | V          |
| Collector-Emitter Voltage   | $V_{CEO}$    | 50      | V          |
| Emitter-Base Voltage        | $V_{EBO}$    | 6       | V          |
| Collector Current           | $I_C$        | 3       | A          |
| Base Current                | $I_B$        | 0.6     | A          |
| Collector Power Dissipation | $P_C$        | 500     | mW         |
| Collector Power Dissipation | $P_C$ (Note) | 1000    | mW         |
| Junction Temperature        | $T_j$        | 150     | $^\circ C$ |
| Storage Temperature Range   | $T_{stg}$    | -55~150 | $^\circ C$ |

(Note) : Mounted on ceramic substrate ( $250mm^2 \times 0.8t$ )

MARKING



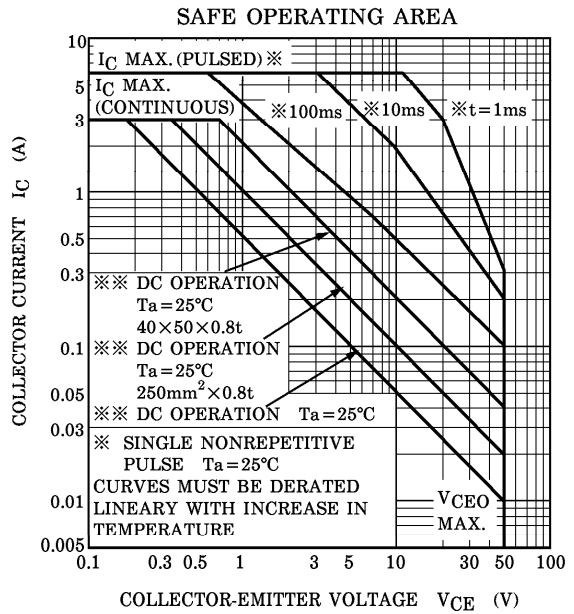
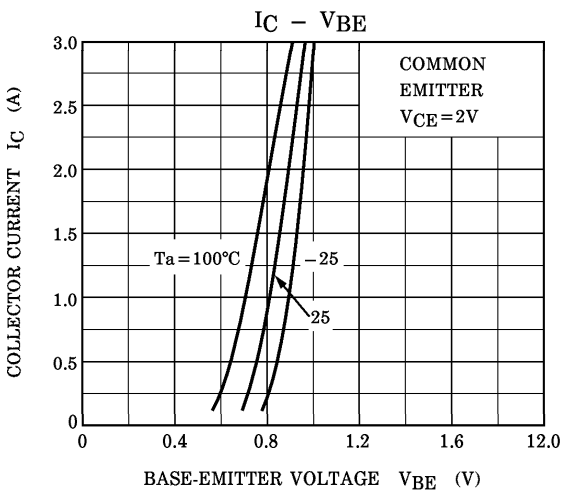
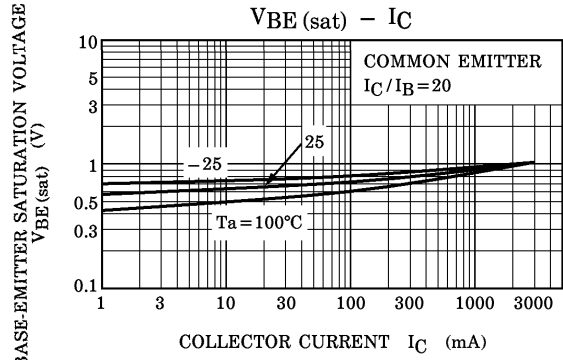
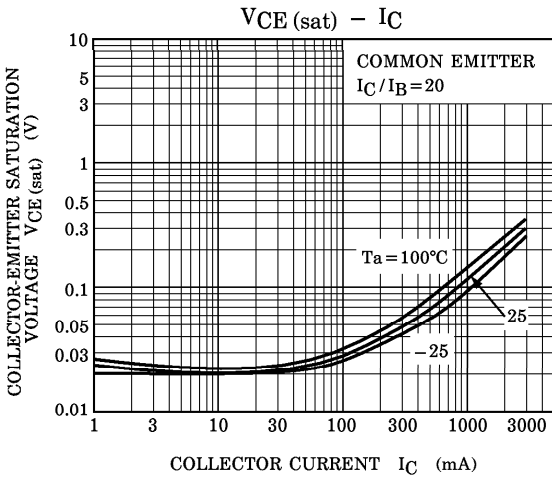
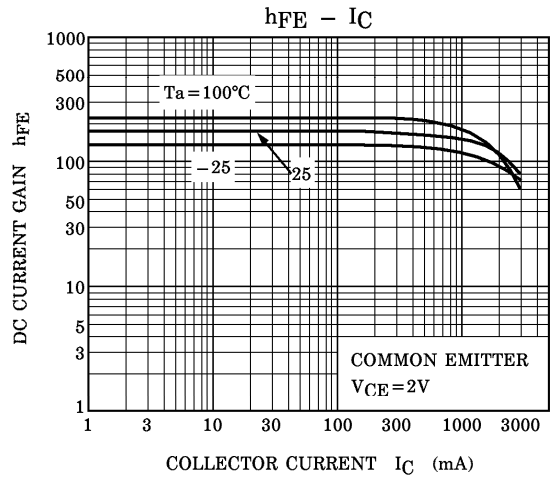
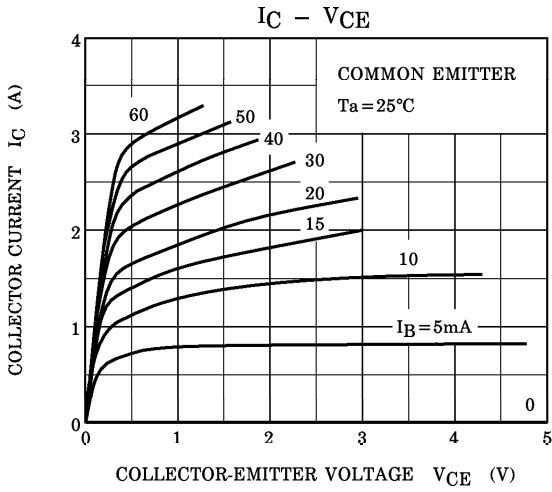
Unit in mm

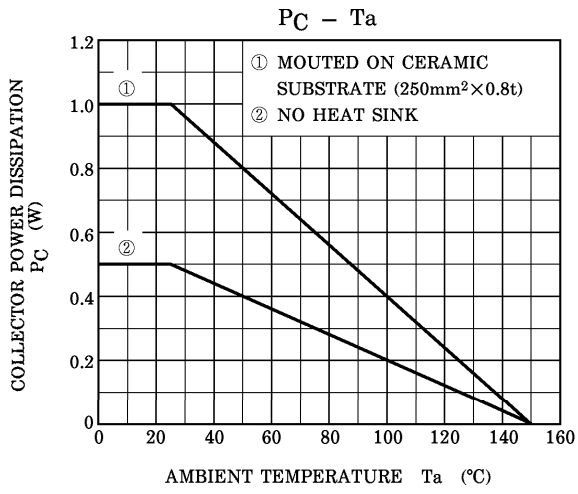


Weight : 0.05g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC                       |              | SYMBOL                | TEST CONDITION   | MIN.  | TYP. | MAX. | UNIT |
|--------------------------------------|--------------|-----------------------|--|---|------|------|------|
| Collector Cut-off Current            |              | ICBO                  | V <sub>CB</sub> = 80V, I <sub>E</sub> = 0  | —   | —    | 0.1  | μA   |
| Emitter Cut-off Current              |              | IEBO                  | V <sub>EB</sub> = 6V, I <sub>C</sub> = 0   | —   | —    | 0.1  | μA   |
| Collector-Emitter Breakdown Voltage  |              | V (BR) CEO            | I <sub>C</sub> = 10mA, I <sub>B</sub> = 0  | 50  | —    | —    | V    |
| DC Current Gain                      |              | h <sub>FE</sub> (1)   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 100mA   | 120   | —    | 400  |      |
|                                      |              | h <sub>FE</sub> (2)   | V <sub>CE</sub> = 2V, I <sub>C</sub> = 2A  | 40  | —    | —    |      |
| Collector-Emitter Saturation Voltage |              | V <sub>CE</sub> (sat) | I <sub>C</sub> = 1.5A, I <sub>B</sub> = 75mA   | —   | —    | 0.5  | V    |
| Base-Emitter Saturation Voltage      |              | V <sub>BE</sub> (sat) | I <sub>C</sub> = 1.5A, I <sub>B</sub> = 75mA   | —   | —    | 1.2  | V    |
| Transition Frequency                 |              | f <sub>T</sub>        | V <sub>CE</sub> = 2V, I <sub>C</sub> = 100mA   | —   | 100  | —    | MHz  |
| Collector Output Capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz                                    | —   | 20   | —    | pF   |
| Switching Time                       | Turn-on Time | t <sub>on</sub>       | <p>20μs<br/>I<sub>B1</sub><br/>INPUT<br/>I<sub>B2</sub><br/>OUTPUT<br/>20Ω<br/>30V</p> | —   | 0.1  | —    | μs   |
|                                      | Storage Time | t <sub>stg</sub>      |  | —   | 0.5  | —    |      |
|                                      | Fall Time    | t <sub>f</sub>        |  | I <sub>B1</sub> = -I <sub>B2</sub> = 75mA,<br>DUTY CYCLE ≤ 1% | —    | 0.1  |      |





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